

NXH80B120L2Q0

1200 V40 AIGBT + 1200 V30 A

NXH80B120L2Q0SG 40A/1200V IGBT 30A/1200V IGBT 25A/1600V 25A/1600V

- IGBT Specifications: VCE(SAT) = 2.2 V, ESW = 2830 μ J
- 25 A / 1600 V Bypass and Anti-parallel Diodes
- Si Rectifier Specification: VF = 2.4 V, IRRM = 53 A
- Solderable Pins
- Dual Boost 40 A / 1200 V IGBT + Si Rectifier Module
- Thermistor
- Solar Inverter Boost Stage
- Fast IGBT with low VCE(SAT) for high efficiency
- Low VF bypass diodes for excellent efficiency in bypass mode
- Si Diode for moderate speed switching
- Easy mounting
- Solar Inverter
- UPS